# 74HC2G00-Q100; 74HCT2G00-Q100

Dual 2-input NAND gate Rev. 1 — 7 November 2013

**Product data sheet** 

### 1. General description

The 74HC2G00-Q100; 74HCT2G00-Q100 is a dual 2-input NAND gate. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V<sub>CC</sub>.

This product has been gualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

#### Features and benefits 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
  - For 74HC2G00-Q100: CMOS level
  - For 74HCT2G00-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)

#### **Ordering information** 3.

#### Table 1. **Ordering information**

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G00DP-Q100	–40 °C to +125 °C	TSSOP8 plastic thin shrink small outline package;		SOT505-2
74HCT2G00DP-Q100			8 leads; body width 3 mm; lead length 0.5 mm	
74HC2G00DC-Q100	–40 °C to +125 °C	VSSOP8 plastic very thin shrink small outline package;		SOT765-1
74HCT2G00DC-Q100			8 leads; body width 2.3 mm	

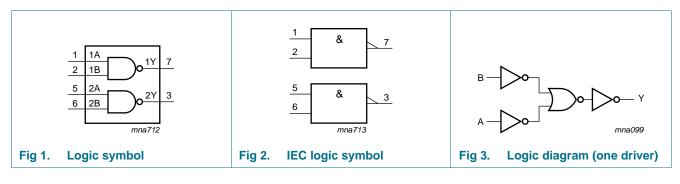


### 4. Marking

Table 2.   Marking code	
Type number	Marking code <sup>[1]</sup>
74HC2G00DP-Q100	H00
74HCT2G00DP-Q100	T00
74HC2G00DC-Q100	H00
74HCT2G00DC-Q100	T00

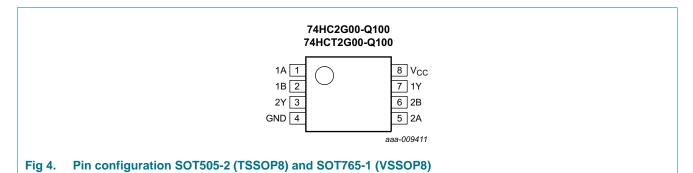
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram



## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V <sub>CC</sub>	8	supply voltage

**Product data sheet** 

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## 7. Functional description

Table 4.	Function table		
Input			Output
nA		nB	nY
L		L	Н
L		Н	Н
Н		L	Н
Н		Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
Ι <sub>ΟΚ</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I <sub>O</sub>	output current	$V_{O} = -0.5 \text{ V} \text{ to} (V_{CC} + 0.5 \text{ V})$	<u>[1]</u> _	25	mA
I <sub>CC</sub>	supply current		<u>[1]</u> _	50	mA
I <sub>GND</sub>	ground current		<u>[1]</u> –50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
PD	dynamic power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	[2] _	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.

### 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74H	C2G00-0	Q100	74H	CT2G00-	Q100	Unit	
			Min	Тур	Max	Min	Тур	Max	1	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V	
VI	input voltage		0	-	$V_{CC}$	0	-	V <sub>CC</sub>	V	
Vo	output voltage		0	-	$V_{CC}$	0	-	V <sub>CC</sub>	V	
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C	
Δt/ΔV	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V	
	and fall rate	$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V	
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V	

### **10. Static characteristics**

#### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

Symbol	Parameter	Conditions	-40	°C to +8	35 °C	_40 °C	to +125 °C	Unit
			Min	Тур	Max	Min	Max	
74HC2G0	0-Q100							
	HIGH-level input	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V
	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V
	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	V
		$I_O$ = -20 $\mu$ A; $V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		$I_O$ = -4.0 mA; $V_{CC}$ = 4.5 V	4.13	4.32	-	3.7	-	V
		$I_O$ = -5.2 mA; $V_{CC}$ = 6.0 V	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O}$ = 20 $\mu$ A; $V_{CC}$ = 2.0 V	-	0	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current	per input pin; V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	10	-	20	μA
Cı	input capacitance		-	1.5	-	-	-	pF

**Dual 2-input NAND gate** 

#### Table 7. Static characteristics ... continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25 \ ^{\circ}C$ .

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	–40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	
74HCT2G	00-Q100							
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
VIL	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_{O}$ = -4.0 mA; $V_{CC}$ = 4.5 V	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.1	-	0.1	V
		$I_{O}$ = 4.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current		-	-	10	-	20	μΑ
$\Delta I_{CC}$	additional supply current	per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; I <sub>O</sub> = 0 A	-	-	375	-	410	μA
CI	input capacitance		-	1.5	-	-	-	pF

### **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); all typical values are measured at  $T_{amb} = 25$  °C; for test circuit, see <u>Figure 6</u>.

Symbol	Parameter	Conditions		–40 °C to +85 °C		-40 °C t	o +125 °C	Unit	
				Min	Тур	Max	Min	Max	
74HC2G	00-Q100								
t <sub>pd</sub>	propagation delay	nA and nB to nY; see Figure 5	[1]						
		$V_{CC} = 2.0 V$		-	25	95	-	110	ns
		$V_{CC} = 4.5 V$		-	9	19	-	22	ns
		$V_{CC} = 6.0 V$		-	7	16	-	20	ns
t <sub>t</sub>	transition time	see Figure 5	[2]						
		$V_{CC} = 2.0 V$		-	18	95	-	125	ns
		$V_{CC} = 4.5 V$		-	6	19	-	25	ns
		$V_{CC} = 6.0 V$		-	5	16	-	20	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	[3]	-	10	-	-	-	pF

#### Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); all typical values are measured at  $T_{amb} = 25 \text{ °C}$ ; for test circuit, see Figure 6.

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	–40 °C t	Unit	
				Min	Тур	Max	Min	Max	
74HCT2	G00-Q100								
t <sub>pd</sub>	propagation delay	nA and nB to nY; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	12	24	-	29	ns
t <sub>t</sub>	transition time	$V_{CC} = 4.5 \text{ V}; \text{ see } \frac{\text{Figure 5}}{1000}$	[2]	-	6	19	-	22	ns
C <sub>PD</sub>	power dissipation capacitance	$V_{\rm I}$ = GND to $V_{\rm CC}$ – 1.5 V	[3]	-	10	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

- [2]  $t_t$  is the same as  $t_{TLH}$  and  $t_{THL}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

### 12. Waveforms

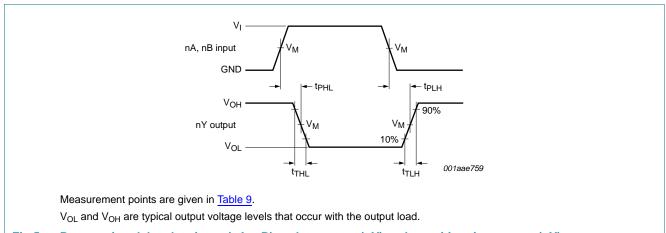
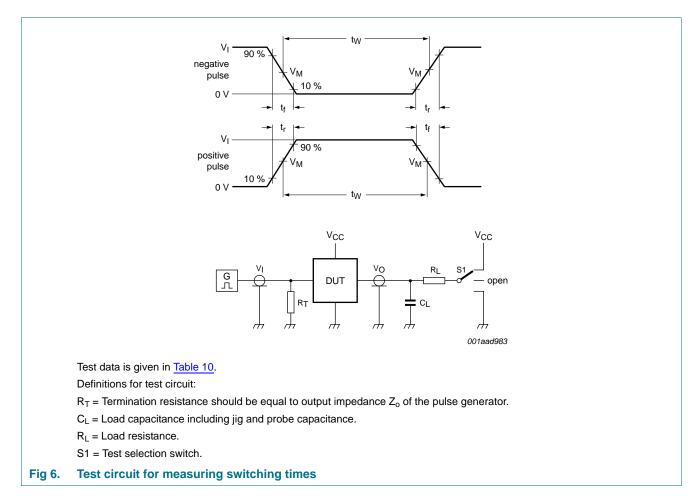


Fig 5. Propagation delay data input (nA, nB) to data output (nY) and transition time output (nY)

#### Table 9. Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74HC2G00-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT2G00-Q100	1.3 V	1.3 V

#### **Dual 2-input NAND gate**

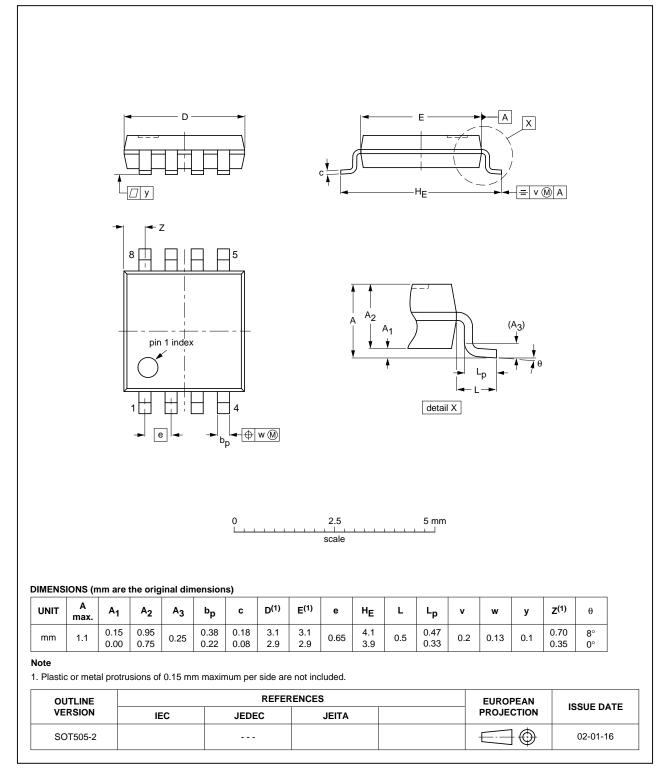


#### Table 10. Test data

Туре	Input		Load	S1 position	
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	RL	t <sub>PHL</sub> , t <sub>PLH</sub>
74HC2G00-Q100	V <sub>CC</sub>	≤ 6 ns	50 pF	1 kΩ	open
74HCT2G00-Q100	3 V	≤ 6 ns	50 pF	1 kΩ	open

### 13. Package outline



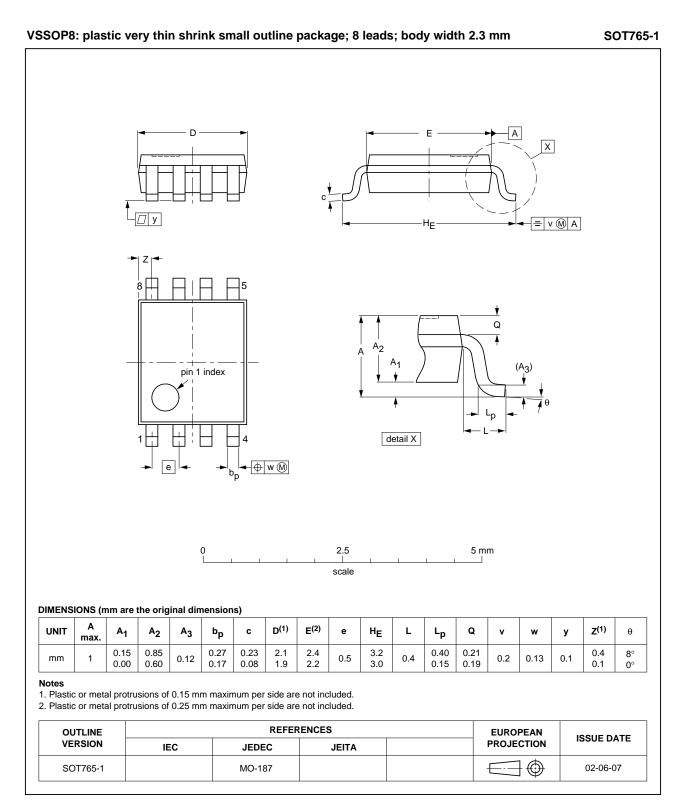


#### Fig 7. Package outline SOT505-2 (TSSOP8)

74HC\_HCT2G00\_Q100

# 74HC2G00-Q100; 74HCT2G00-Q100

**Dual 2-input NAND gate** 



#### Fig 8. Package outline SOT765-1 (VSSOP8)

74HC\_HCT2G00\_Q100

### 14. Abbreviations

Table 11. Abbreviations			
Acronym	Description		
CMOS	Complementary Metal-Oxide Semiconductor		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
MM	Machine Model		
TTL	Transistor-Transistor Logic		

## 15. Revision history

#### Table 12.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G00_Q100 v.1	20131107	Product data sheet	-	-

### **16. Legal information**

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
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